

FDB6021P

20V P-Channel 1.8V Specified PowerTrench® MOSFET

General Description

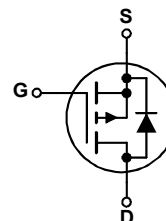
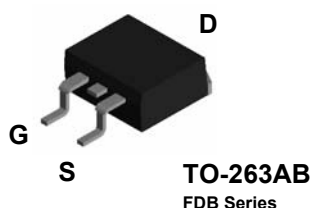
This P-Channel power MOSFET uses Fairchild's low voltage PowerTrench process. It has been optimized for power management applications.

Applications

- Battery management
- Load switch
- Voltage regulator

Features

- -28 A, -20 V. $R_{DS(ON)} = 30\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
 $R_{DS(ON)} = 40\text{ m}\Omega @ V_{GS} = 2.5\text{ V}$
 $R_{DS(ON)} = 65\text{ m}\Omega @ V_{GS} = 1.8\text{ V}$
- Critical DC electrical parameters specified at elevated temperature
- High performance trench technology for extremely low $R_{DS(ON)}$
- 175°C maximum junction temperature rating



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 8	V
I_D	Drain Current – Continuous (Note 1)	-28	A
	– Pulsed (Note 1)	-80	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	37	W
	Derate above 25°C	0.25	W/°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-65 to +175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDB6021P	FDB6021P	13"	24mm	800 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain–Source Breakdown Voltage	V _{GS} = 0 V, I _D = –250 μA	–20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = –250 μA,Referenced to 25°C		–16		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = –16 V, V _{GS} = 0 V			–1	μA
I _{GSSF}	Gate–Body Leakage, Forward	V _{GS} = 8 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate–Body Leakage, Reverse	V _{GS} = –8 V V _{DS} = 0 V			–100	nA
On Characteristics (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = –250 μA	–0.4	–0.7	–1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = –250 μA,Referenced to 25°C		3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = –4.5 V, I _D = –14 A V _{GS} = –2.5 V, I _D = –12 A V _{GS} = –1.8 V, I _D = –10 A V _{GS} = –4.5V, I _D = –14 A, T _J =125°C		24 31 50 30	30 40 65 42	mΩ
I _{D(on)}	On–State Drain Current	V _{GS} = –4.5 V, V _{DS} = –5 V	–40			A
g _{FS}	Forward Transconductance	V _{DS} = –5 V, I _D = –14 A		33		S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = –10 V, V _{GS} = 0 V, f = 1.0 MHz		1890		pF
C _{oss}	Output Capacitance			302		pF
C _{rss}	Reverse Transfer Capacitance			124		pF
Switching Characteristics (Note 2)						
t _{d(on)}	Turn–On Delay Time	V _{DD} = –10 V, I _D = –1 A, V _{GS} = –4.5 V, R _{GEN} = 6 Ω		13	23	ns
t _r	Turn–On Rise Time			10	20	ns
t _{d(off)}	Turn–Off Delay Time			80	128	ns
t _f	Turn–Off Fall Time			50	80	ns
Q _g	Total Gate Charge	V _{DS} = –10 V, I _D = –14 A, V _{GS} = –4.5 V		20	28	nC
Q _{gs}	Gate–Source Charge			4		nC
Q _{gd}	Gate–Drain Charge			7		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain–Source Diode Forward Current				–28	A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = –14 A		–0.9	–1.3	V

Notes:1. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

2. Calculated continuous current based on maximum allowable junction temperature. Actual maximum continuous current limited by package constraints to 75A

Typical Characteristics

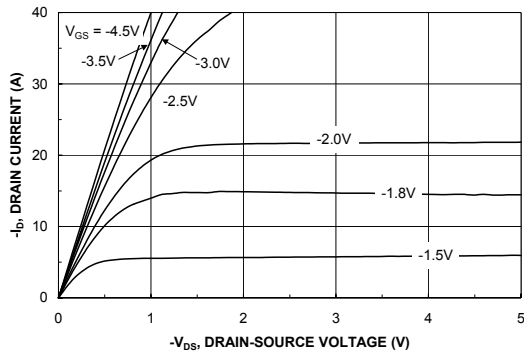


Figure 1. On-Region Characteristics.

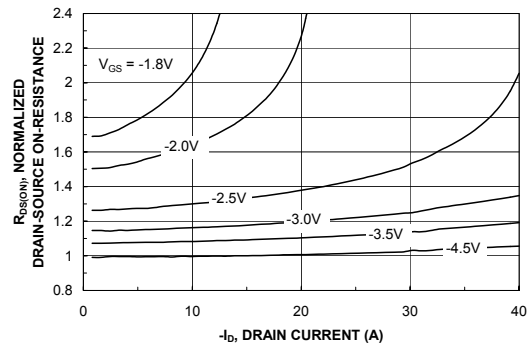


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

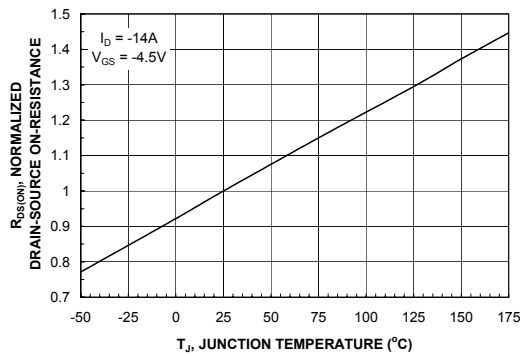


Figure 3. On-Resistance Variation with Temperature.

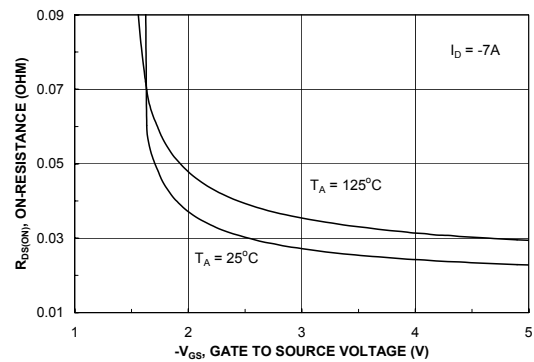


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

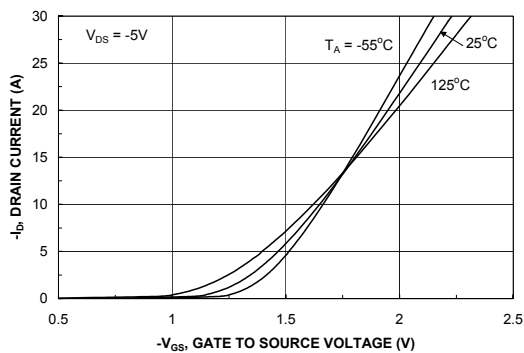


Figure 5. Transfer Characteristics.

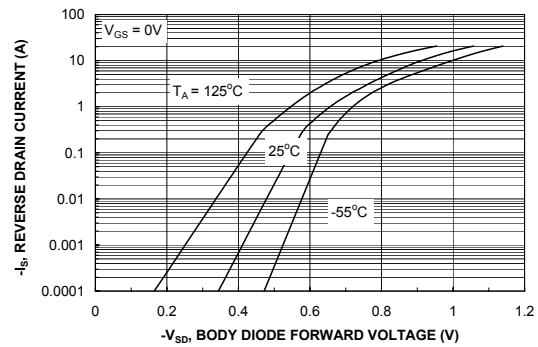


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

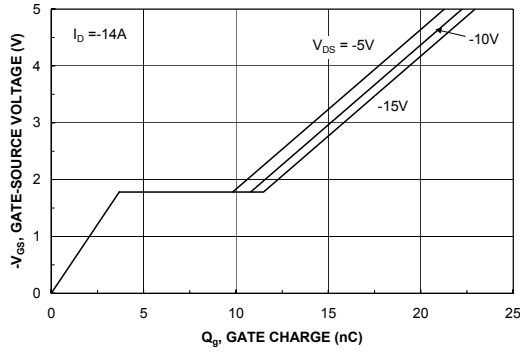


Figure 7. Gate Charge Characteristics.

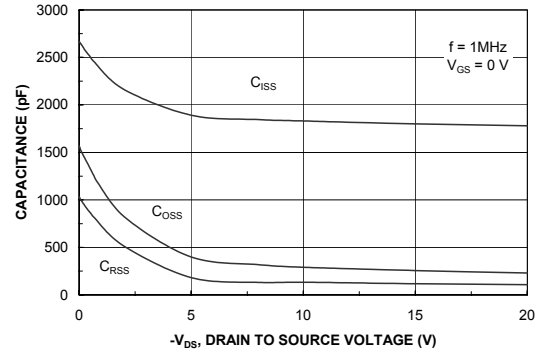


Figure 8. Capacitance Characteristics.

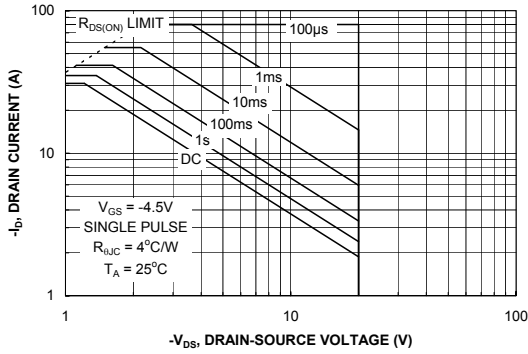


Figure 9. Maximum Safe Operating Area.

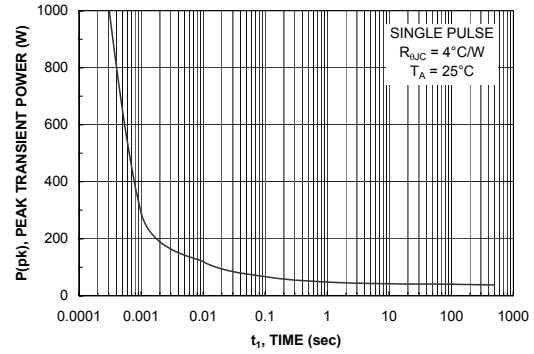


Figure 10. Single Pulse Maximum Power Dissipation.

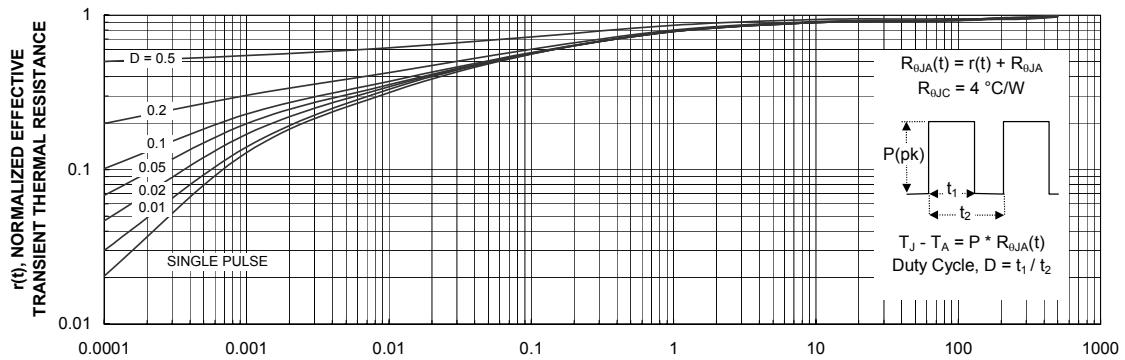


Figure 11. Transient Thermal Response Curve.

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